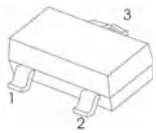
FEATURES

- Epitaxial Planar Die Construction
- Complementary NPN Types Available (MMBTA55 / MMBTA56)
- Ideal for Low Power Amplification and Switching

SOT-23



1.BASE
2.EMITTER
3.COLLECTOR

MMBTA55 Marking: 2H
MMBTA56 Marking: 2GM





MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	MMBTA55	MMBTA56	Unit
Collector-Base Voltage	V_{CBO}	-60	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	-80	V
Emitter-Base Voltage	V_{EBO}	-4.0		V
Collector Current - Continuous	I_C	-500		mA
Power Dissipation	P_d	300		mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417		°C/W
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150		°C

Electrical Characteristics Ta = 25℃

Characteristic		Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	MMBTA55 MMBTA56	$V_{(BR)CBO}$	-60 -80	—	V	I_C = -100μA, I_E = 0
Collector-Emitter Breakdown Voltage	MMBTA55 MMBTA56	$V_{(BR)CEO}$	-60 -80	—	V	I_C = -1.0mA, I_B = 0
Emitter-Base Breakdown Voltage		$V_{(BR)EBO}$	-4.0	—	V	I_E = -100μA, I_C = 0
Collector Cutoff Current	MMBTA55 MMBTA56	I_{CBO}	—	-100	nA	V_{CB} = -60V, I_E = 0 V_{CB} = -80V, I_E = 0
Collector Cutoff Current	MMBTA55 MMBTA56	I_{CEX}	—	-100	nA	V_{CE} = -60V, I_{BO} = 0V V_{CE} = -80V, I_{BO} = 0V
ON CHARACTERISTICS						
DC Current Gain		h_{FE}	100	—	—	I_C = -10mA, V_{CE} = -1.0V I_C = -100mA, V_{CE} = -1.0V
Collector-Emitter Saturation Voltage		$V_{CE(SAT)}$	—	-0.25	V	I_C = -100mA, I_B = -10mA
Base-Emitter Saturation Voltage		$V_{BE(SAT)}$	—	-1.2	V	I_C = -100mA, V_{CE} = -1.0V
SMALL SIGNAL CHARACTERISTICS						
Current Gain-Bandwidth Product		f_T	50	—	MHz	V_{CE} = -1.0V, I_C = -100mA, f = 100MHz

RATING AND CHARACTERISTIC CURVES

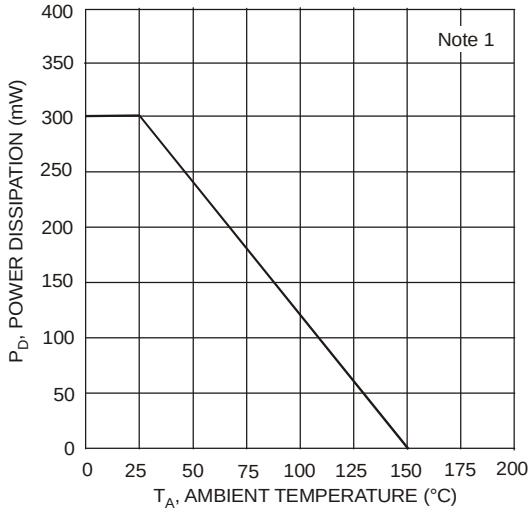


Fig. 1 Max Power Dissipation vs Ambient Temperature

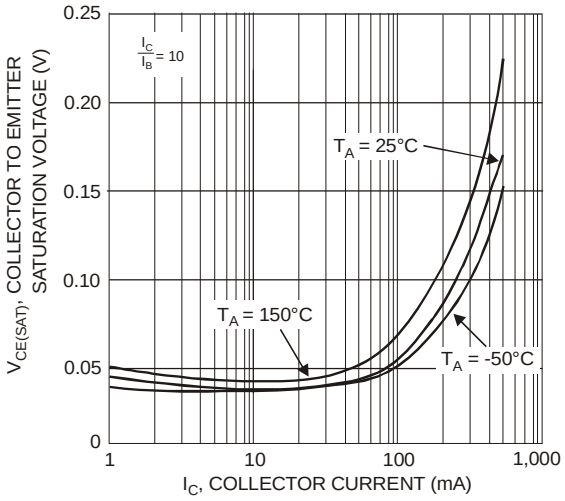


Fig. 2 Collector Emitter Saturation Voltage vs. Collector Current

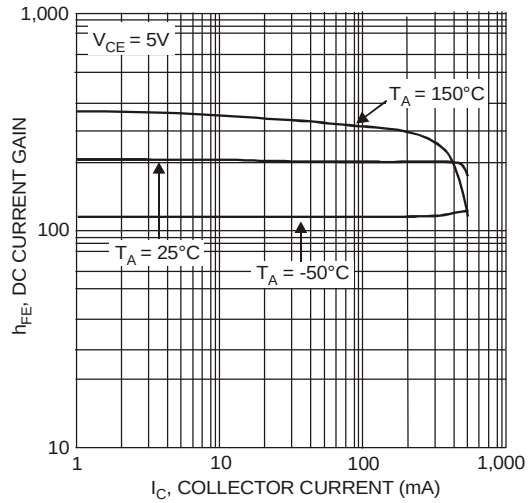


Fig. 3 DC Current Gain vs. Collector Current

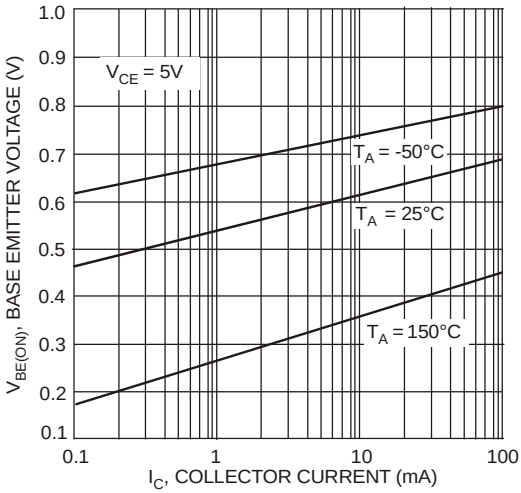
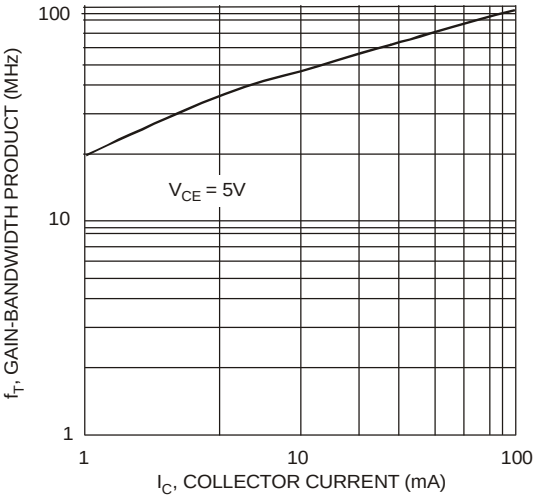


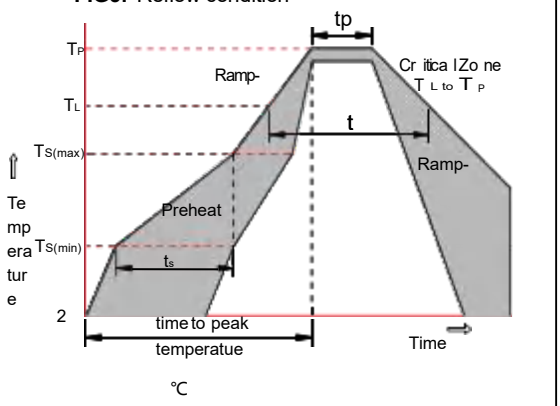
Fig. 4 Base Emitter Voltage vs. Collector Current



Soldering parameters

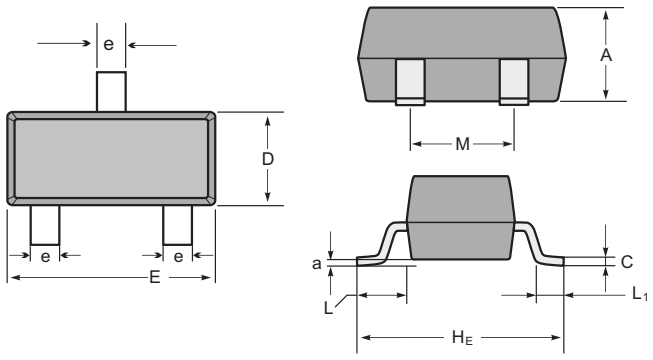
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

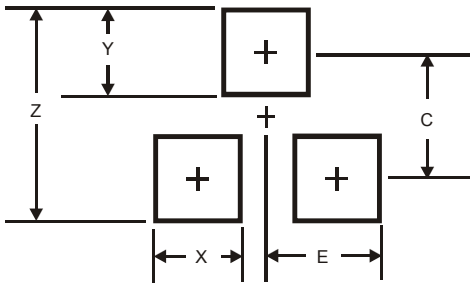
FIG5: Reflow condition



Package Dimensions & Suggested Pad Layout

SOT23





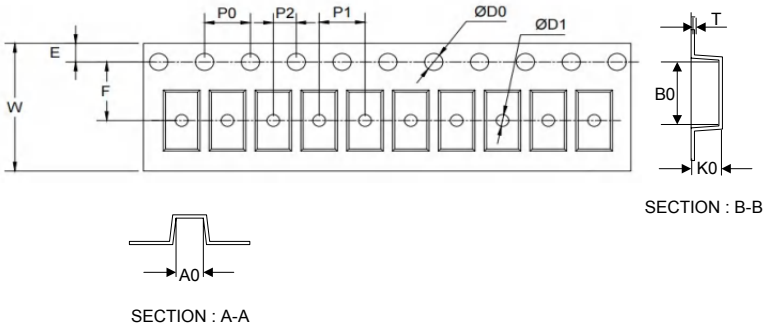
SOT-23 mechanical data

UNIT		A	C	D	E	H_E	e	M	L	L_1	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Dimensions	SOT23
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

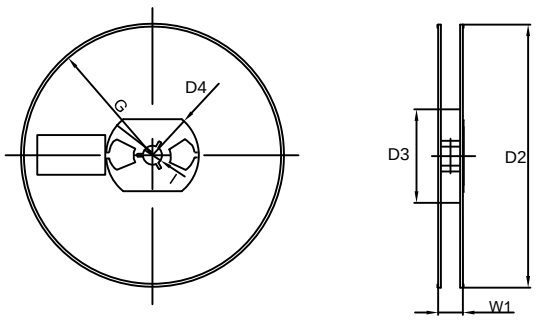
Tape & rell specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.10
P1	4.00±0.10
P2	2.00±0.10
D0	1.55±0.10
D1	1.05±0.10
E	1.55±0.10
F	3.60±0.10
W	8.00±0.10
A0	3.80±0.20
B0	3.25±0.20
K0	1.45±0.10
T	0.25±0.05

7” Reel



D2	178.0±3.0
D3	55Min.
D4	R24.0±3.0
G	R82.0±3.0
I	13.0±2.0
W1	11.0±3.0
Quantity: 3000PCS	